# **HOLTO**

# HTH8G02P550S(B)-T 550W, 1.8 - 200 MHz LDMOS Amplifier

Product datasheet

### **Description**

The HTH8G02P550S(B)-T is an unmatched discrete LDMOS Power Amplifier with 550W saturated output power covering frequency range from 1.8 - 200 MHz.

#### **Features**

Operating Frequency Range: 1.8 - 200 MHz

Operating Drain Voltage: 28-50V

• Saturation Output Power: 550W

• Internally Unmatched device

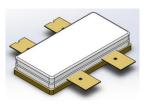
- Excellent thermal stability due to low thermal resistance package
- Enhanced robustness design without device degradation
- Internally integrated enhanced ESD design

## **Applications**

- HF VHF band High Power Amplifier
- Broadcasting transmitter
- Industrial Scientific Medical (ISM)
  - Laser generation
  - Plasma generation
  - Particle accelerators
  - MRI, RF ablation and skin treatment
  - Industrial heating, welding and drying systems

## **Ordering Information**

Part Number	Description
HTH8G02P550S(B)-T	Tray Package
HTH8G02P550S(B)-T EVB	100 MHz EVB

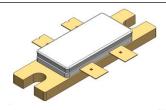


#### ACS2110S-4L-T

Earless Flanged Balanced

Air Cavity Spliced Package; 4 Leads





#### ACS2110B-4L-T

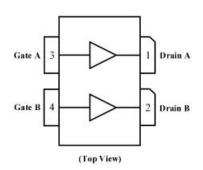


RoHS

Flanged Balanced

Air Cavity Spliced Package; 4 Leads, 2 Mounting holes

HTH8G02P550SB-T



Note: Exposed backside of the package is the source terminal for the transistor

**Pin Connections** 

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# **Typical Performance**

#### **RF Characteristics (CW)**

Freq (MHz)	P3dB (dBm)	P3dB (W)	Gain (dB)	Eff(%)@P3dB
100	57.54	558	25.28	70

Test conditions unless otherwise noted: 25 °C, VDD = +50Vdc, IDQ =300mA test on HOTLO Application Board

#### **RF Characteristics (Pulsed-CW)**

Freq (MHz)	P3dB (dBm)	P3dB (W)	Gain (dB)	Eff(%)@P3dB
100	57.82	580	25.32	75

Test conditions unless otherwise noted: 25 °C, VDD = +50Vdc, IDQ = 300mA, PW = 100us, DC = 10% test on HOTLO Application Board

# **Absolute Maximum Ratings**

Parameter	Range/Value	Unit
Drain voltage (VDSS)	-0.5 to +135	V
Gate voltage (V <sub>GS</sub> )	-5 to +10	V
Operating Voltage (VDS)	0 to +50	
Storage Temperature (Tstg)	-55 to +150	°C
Junction Temperature (T <sub>J</sub> )	-40 to +225	°C

## **Electrical Specification**

#### **DC Characteristics**

Parameter	Conditions	Min	Тур	Max	Unit
Breakdown Voltage V(BR)DSS	Vgs=0V, Ids=380uA	-	135	-	V
Gate-Source Threshold	\/dc_10\/ \ldc_200\	1 5	2.25	2.0	V
Voltage V <sub>GS(th)</sub>	Vds=10V, Ids=380uA	1.5	2.25	2.9	V
Drain Leakage Current loss	Vgs=0V, Vds=50V	-	1	10	uA
Gate Leakage Current IGSS	Vgs=5V, Vds=0V	-	0.1	1	uA

#### **Load Mismatch Test**

Condition	Test Result
VSWR=65:1 at all Phase Angles, $V_{DD}$ = +50Vdc, $I_{DQ}$ =300mA, Pout = 550W,	No Device
PW = 200us, DC= 20%, freq@100 MHz	Degradation

# HTH8G02P550S(B)-T



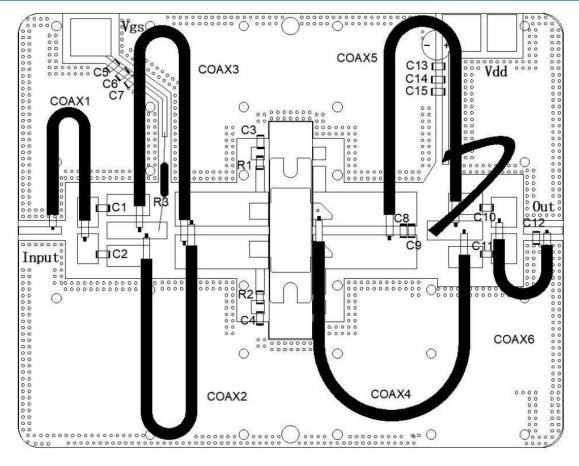
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#### **Thermal Information**

Parameter	Condition	Value (Typ)	Unit
Thermal Resistance	TFLANGE= $45^{\circ}$ C, $V_{DD} = +50$ Vdc, $I_{DQ}=300$ mA,		
	CW, P <sub>AVG</sub> = 57.4 dBm (550W),	0.12	°C /W
Junction to Case (Rтн)	Freq@100 MHz		

# HTH8G02P550S(B)-T 100 MHz Reference Design



**EVB Layout** 

# Bill of Materials (BoM) - HTH8G02P550S(B)-T 100 MHz Reference Design

Reference	Value	Description	Manufacturer	P/N
Q1	_	550W, 1.8 - 200 MHz	Holto	HTH8G02P550S(B)-T
Qı		LDMOS PA	HOITO	H1H8GUZP35U3(B)-1
C5,C13	4u7F	MLCC	Murata	GRM31CR71H475KA12L
C1,C2,C10,C11	300pF	MLCC	ATC	ATC100B301JT
C8	10pF	MLCC	ATC	ATC100B100JT

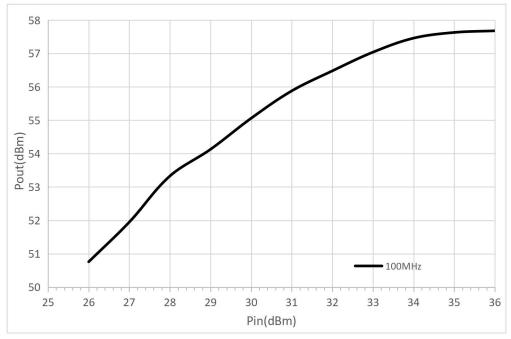
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C9,C12	4p7F	MLCC	ATC	ATC100B4R7JT
C3,C4,C6,C14	1nF	MLCC	Murata	GR321AD72E102KW01D
C7,C15	100pF	MLCC	Murata	GRM1885C1H101JA01
R3	820Ω	Wire Resistor	-	-
Coax 2,3	16.7Ω 4:1,110 mm		-	-
Coax 4,5	16.7Ω 4:1, 100 mm		-	-
Coax 1	50Ω 2:1,100 mm		-	-
Coax 6	50Ω 2:1, 40mm		-	-
PCB RF35 (er = 3.5), 30 mil (0.762 mm), 35 μm (1oz)				

# **Performance Plots**



Pulsed CW, Pout vs Pin

# 550W, 1.8 - 200 MHz LDMOS Amplifier

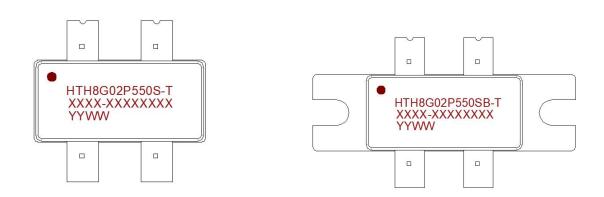
Product datasheet



Pulsed CW, Gain and Efficiency vs Pout

Test conditions unless otherwise noted: 25 °C, VDD = +50dc, IDQ = 300mA, PW = 100us, DC = 10% test on HOTLO Application Board

## **Package Marking and Dimensions**



- Line1 (fixed): Device name in work order
- Line2 (unfixed): Mark Lot Number in work order (Sample: E596-EERA0001)
- Line3 (unfixed): Date Code

This Marking SPEC only stipulates the content of Marking. For marking requirements such as font and size, please refer to the latest version of "Holto Product Printing Specification"

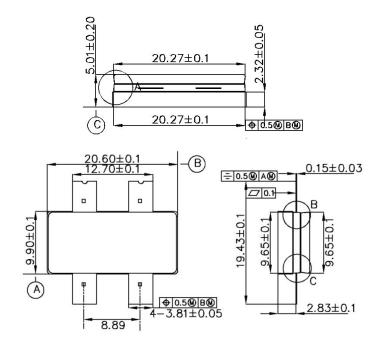
Marking

# HTH8G02P550S(B)-T



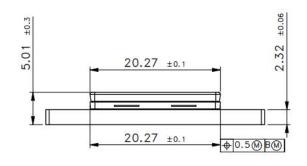


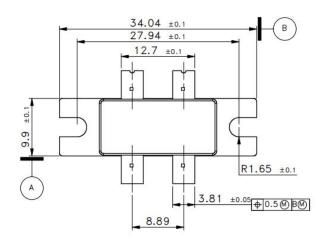
Product datasheet

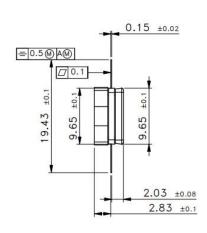


Remark: 1.Unit: mm;

ACS2110S-4L-T; Earless Flanged Balanced Air Cavity Spliced Package; 4 Leads







Remark: 1.Unit: mm;

ACS2110B-4L-T; Flanged Balanced Air Cavity Spliced Package; 2 mounting holes; 4 leads

Package Dimensions

Product datasheet

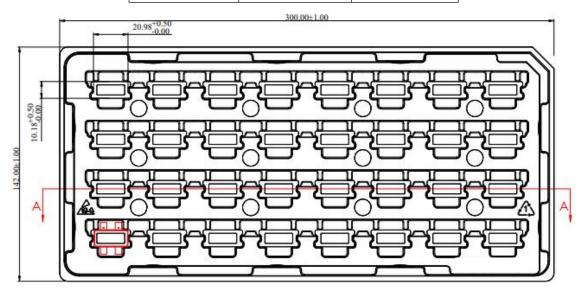


# 550W, 1.8 - 200 MHz LDMOS Amplifier

# **Packing Information**

#### HTH8G02P550S-T:

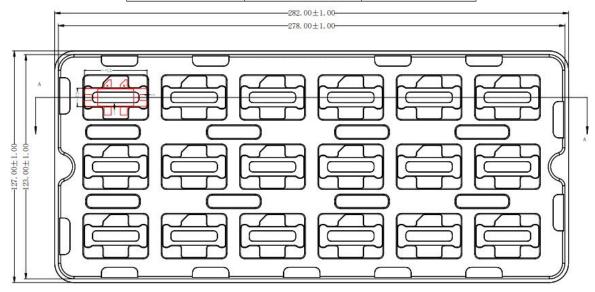
Package Type	Qty/Tray(pcs)	Qty/Box(pcs)
ACS2110S-4L-T	32	160



HTH8G02P550S-T Packaging Descriptions

### HTH8G02P550SB-T:

Package Type	Qty/Tray(pcs)	Qty/Box(pcs)
ACS2110B-4L-T	18	90



HTH8G02P550SB-T Packaging Descriptions

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# **Handling Precautions**

Parameter	Rating	Standard
ESD – Human Body Model (HBM)	Class 1B	JESD22-A114
ESD – Human Body Model (MM)	Class A	EIA/JESD22-A115
ESD – Charged Device Model (CDM)	Class III	JESD22-C101



### **RoHS Compliance**

This product is compliant with the 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment), as amended by Directive 2015/863/EU.

#### **Datasheet Status**

Document status	Product status	Definition
Objective Datasheet	Design simulation	Product objective specification
Preliminary Datasheet	Customer sample	Engineering samples and first test results
Product Datasheet	Mass production	Final product specification

### **Abbreviations**

Acronym	Definition
LDMOS	Laterally-Diffused Metal-Oxide Semiconductor
CW	Continuous Waveform

## **Revision history**

Document ID	Datasheet Status	Release Date	Revision Version
Rev 1.0	Preliminary	Dec. 2021	Preliminary
Rev 1.1	Product	March 2023	New format based on English version datasheet
Rev 2.0	Product	Sept.2023	Update TBD information
Rev 2.1	Product	Apr.2023	Update package information

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#### **Contact Information**

For the latest specifications, additional product information, worldwide sales and distribution locations and information about HOTLO:

• Web: <u>www.andesource.com</u>

• Email: andehk@andesource.com

For technical questions and application information:

Email:andetech@andesource.com

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